

SEMICONDUCTOR ON INSULATOR DEVICE
ARCHITECTURE AND METHOD OF CONSTRUCTION

ABSTRACT OF THE DISCLOSURE

An SOI architecture is provided that comprises an inner substrate 10 which has a buried conductor layer 12 formed on an outer surface thereof. A bonding layer 14 is used to provide a cohesive bond with a buried insulator layer 18. The semiconductor device layer 20 is formed on the outer surface of buried insulator layer 18. An inductive well 22 can be formed to provide a platform for the formation of inductive devices 34 within an inductive region 26.